

Dedicated to the memory of Prof. M. Sheinkman effect of ultrasonic treatment on the defect structure of the Si-SiO₂ system

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Kropman, Daniel; Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos Physica status solidi (c) 2011 / p. 694-696 : ill <https://www.sciencedirect.com/science/article/pii/S0040609009014564>

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Stress relaxation mechanism by strain in the Si-SiO₂ system and its influence on the interface properties

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